Switch-mode Power Rectifier 60 V, 30 A

MBR30L60CTG, MBRF30L60CTG

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capability
- 30 A Total (15 A Per Diode Leg)
- Guard-Ring for Stress Protection
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics:

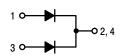
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams (TO-220 & TO-220FP)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



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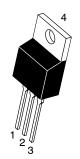
SCHOTTKY BARRIER RECTIFIER 30 AMPERES, 60 VOLTS

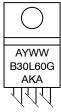


TO-220

CASE 221A

STYLE 6

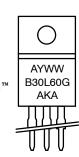




MARKING DIAGRAMS



AKA



A = Assembly Location

Y = Year

WW = Work Week

B30L60 = Device Code

G = Pb-Free Device

ORDERING INFORMATION

= Polarity Designator

See detailed ordering and shipping information on page 2 of this data sheet.

MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	60	V
Average Rectified Forward Current MBR30L60CTG (Rated V_R) T_C = 133°C MBRF30L60CTG (Rated V_R) T_C = 108°C	(Per Leg) (Per Device) (Per Device)	I _{F(AV)}	15 30	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, sing	le phase, 60 Hz)	I _{FSM}	240	А
Operating Junction Temperature (Note 1)		TJ	-55 to +150	°C
Storage Temperature		T _{stg}	-65 to +175	°C
ESD Ratings:	Machine Model = C Human Body Model = 3B		> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance MBR30L60CTG MBRF30L60CTG Junction-to-Case Junction-to-Case Junction-to-Case Junction-to-Case Junction-to-Ambient	$egin{array}{l} R_{ heta JC} \ R_{ heta JC} \ R_{ heta JA} \end{array}$	2.1 70 5.0 75	°C/W

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Тур	Max	Unit
$\label{eq:maximum Instantaneous Forward Voltage (Note 2)} \begin{array}{c} \text{(I}_F = 15 \text{ A, T}_C = 25^\circ\text{C)} \\ \text{(I}_F = 15 \text{ A, T}_C = 125^\circ\text{C)} \\ \text{(I}_F = 30 \text{ A, T}_C = 25^\circ\text{C)} \\ \text{(I}_F = 30 \text{ A, T}_C = 125^\circ\text{C)} \\ \end{array}$	VF	0.57 0.53 0.75 0.70	0.62 0.57 0.81 0.73	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, T_C = 25°C) (Rated DC Voltage, T_C = 125°C)	i _R	137 62	350 110	μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

DEVICE ORDERING INFORMATION

Device Order Number	Package Type	Shipping
MBR30L60CTG	TO-220 (Pb-Free)	50 Units / Rail
MBRF30L60CTG	TO-220FP (Pb-Free)	50 Units / Rail

^{1.} The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

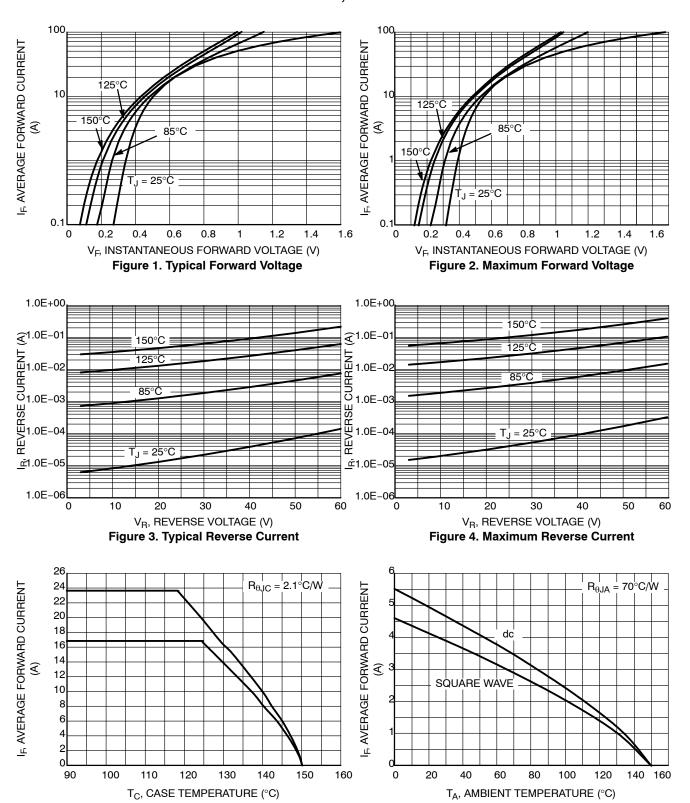


Figure 5. Current Derating, Case per Leg MBR30L60CT

Figure 6. Current Derating, Ambient per Leg MBR30L60CT

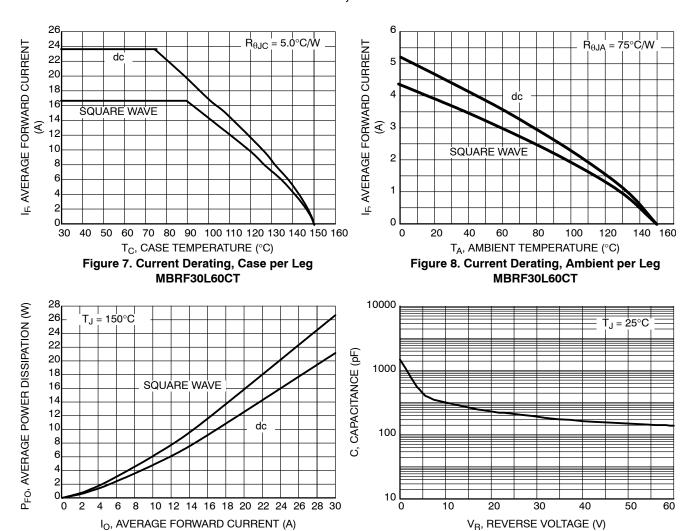


Figure 9. Forward Power Dissipation

Figure 10. Capacitance

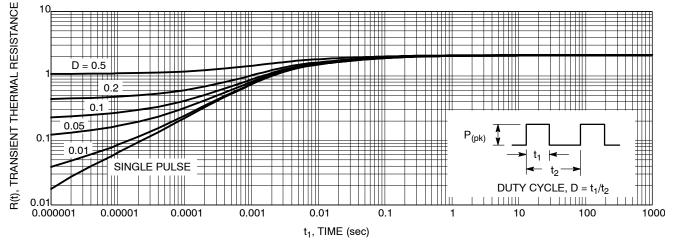


Figure 11. Thermal Response Junction-to-Case, per Leg for MBR30L60CT

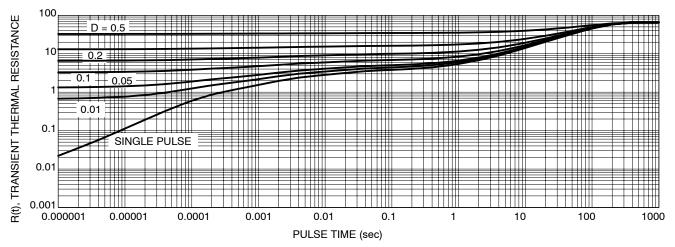


Figure 12. Thermal Response Junction-to-Ambient, per Leg for MBR30L60CT

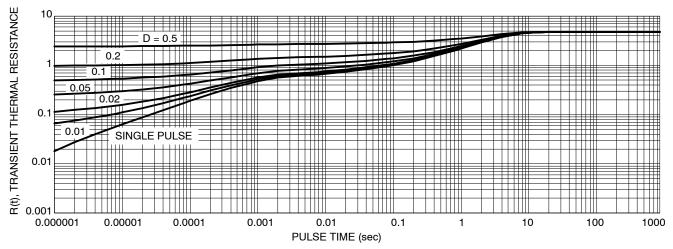


Figure 13. Thermal Response Junction-to-Case, per Leg for MBRF30L60CT

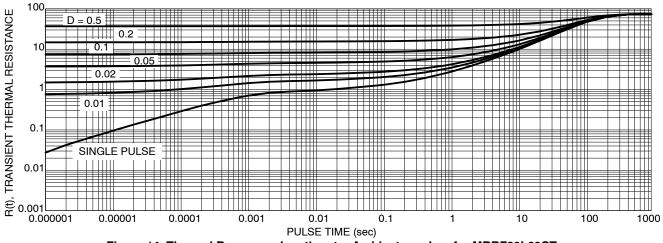
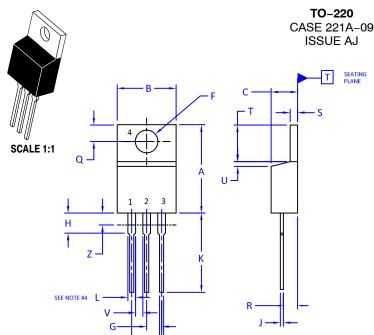


Figure 14. Thermal Response Junction-to-Ambient, per Leg for MBRF30L60CT

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS





DATE 05 NOV 2019

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES

NOTES:

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
К	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:	
PIN 1.	BASE	PIN 1.	BASE	PIN 1.	CATHODE	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	EMITTER	2.	ANODE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	COLLECTOR	3.	GATE	3.	GATE
4.	COLLECTOR	4.	EMITTER	4.	ANODE	4.	MAIN TERMINAL 2
STYLE 5:		STYLE 6:		STYLE 7:		STYLE 8:	
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	CATHODE
2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE
3.	SOURCE	3.	ANODE	3.	CATHODE	3.	EXTERNAL TRIP/DELA
4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE
STYLE 9:		STYLE 10:		STYLE 11:		STYLE 12	:
PIN 1.	GATE	PIN 1.	GATE	PIN 1.	DRAIN	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	SOURCE	2.	SOURCE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	DRAIN	3.	GATE	3.	GATE
4.	COLLECTOR	4.	SOURCE	4.	SOURCE	4.	NOT CONNECTED

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MECHANICAL CASE OUTLINE





SCALE 1:1

3. CATHODE

TO-220 FULLPAK CASE 221D-03 ISSUE K

DATE 27 FEB 2009

0

AYWW

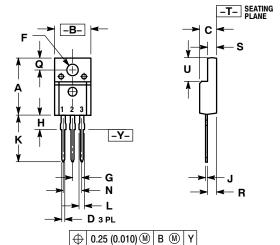
xxxxxxG

AKA

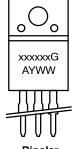
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH
- 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.617	0.635	15.67	16.12
В	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100	BSC	2.54 BSC	
Н	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200	0.200 BSC		BSC
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

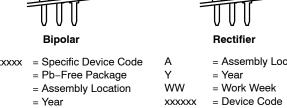
MARKING DIAGRAMS



STYLE 1: PIN 1. GATE STYLE 2: PIN 1. BASE STYLE 3: PIN 1. ANODE 2. COLLECTOR 3. EMITTER CATHODE
 ANODE 2. DRAIN 2. 3. SOURCE STYLE 6: PIN 1. MT 1 2. MT 2 3. GATE STYLE 4: PIN 1. CATHODE STYLE 5: PIN 1. CATHODE 2. ANODE 3. GATE ANODE



= Assembly Location xxxxxx = Specific Device Code G = Pb-Free Package Υ = Year Α = Assembly Location WW = Work Week Υ = Year XXXXXX = Device Code = Work Week = Pb-Free Package WW G AKA = Polarity Designator



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